

N-Channel Power MOSFET

600V, 24A, 165mΩ

FEATURES

- Low $R_{DS(on)}$ to minimize conductive losses
- Low gate charge for fast power switching
- 100% UIS and R_g tested
- ROHS Compliant
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS

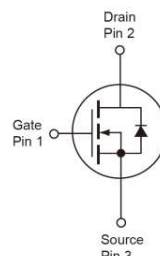
PARAMETER	VALUE	UNIT
V_{DS}	600	V
$R_{DS(on)}$ (max)	165	mΩ
Q_g	47	nC

APPLICATIONS

- PFC Stage
- Power Supply
- AC/DC LED Lighting



ITO-220



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V _{DS}	600	V
Gate-Source Voltage		V _{GS}	±30	V
Continuous Drain Current ^(Note 1)	T _C = 25°C	I _D	24	A
	T _C = 100°C		15	A
Pulsed Drain Current ^(Note 2)		I _{DM}	72	A
Total Power Dissipation @ T _C = 25°C		P _D	89	W
Single Pulse Avalanche Energy ^(Note 3)		E _{AS}	450	mJ
Single Pulse Avalanche Current ^(Note 3)		I _{AS}	4.2	A
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C

THERMAL PERFORMANCE

PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	1.4	$^\circ\text{C/W}$
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	60	$^\circ\text{C/W}$

Thermal Performance Note: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA	BV _{DSS}	600	--	--	V
Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	V _{GS(TH)}	3	3.8	5	V
Gate Body Leakage	V _{GS} = ±30V, V _{DS} = 0V	I _{GSS}	--	--	±100	nA
Zero Gate Voltage Drain Current	V _{DS} = 600V, V _{GS} = 0V	I _{DSS}	--	--	100	μA
Drain-Source On-State Resistance	V _{GS} = 10V, I _D = 5A	R _{DS(on)}	--	143	165	mΩ
Dynamic (Note 5)						
Total Gate Charge	V _{DS} = 480V, I _D = 15A, V _{GS} = 10V	Q _g	--	47	--	nC
Gate-Source Charge		Q _{gs}	--	12	--	
Gate-Drain Charge		Q _{gd}	--	20	--	
Input Capacitance	V _{DS} = 300V, V _{GS} = 0V, f = 1.0MHz	C _{iss}	--	1857	--	pF
Output Capacitance		C _{oss}	--	53	--	
Reverse Transfer Capacitance		C _{rss}	--	10	--	
Gate Resistance	f = 1.0MHz	R _g	--	1.6	3.2	Ω
Switching (Note 6)						
Turn-On Delay Time	V _{DD} = 300V, R _G = 10Ω, I _D = 15A, V _{GS} = 10V	t _{d(on)}	--	30	--	ns
Turn-On Rise Time		t _r	--	50	--	
Turn-Off Delay Time		t _{d(off)}	--	60	--	
Turn-Off Fall Time		t _f	--	12	--	
Source-Drain Diode (Note 4)						
Body-Diode Continuous Forward Current		I _S	--	--	15	A
Body-Diode Pulsed Current		I _{SM}	--	--	60	A
Forward Voltage	I _S = 15A, V _{GS} = 0V	V _{SD}	--	0.8	1.6	V
Reverse Recovery Time	I _S = 7.5A dI _F /dt = 100A/μs	t _{rr}	--	327	--	ns
Reverse Recovery Charge		Q _{rr}	--	4.8	--	μC

Notes:

- Current limited by package.
- Pulse width limited by the maximum junction temperature.
- $L = 50mH, I_{AS} = 4.2A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
- Pulse test: $PW \leq 300\mu s$, duty cycle $\leq 2\%$.
- For DESIGN AID ONLY, not subject to production testing.
- Switching time is essentially independent of operating temperature.

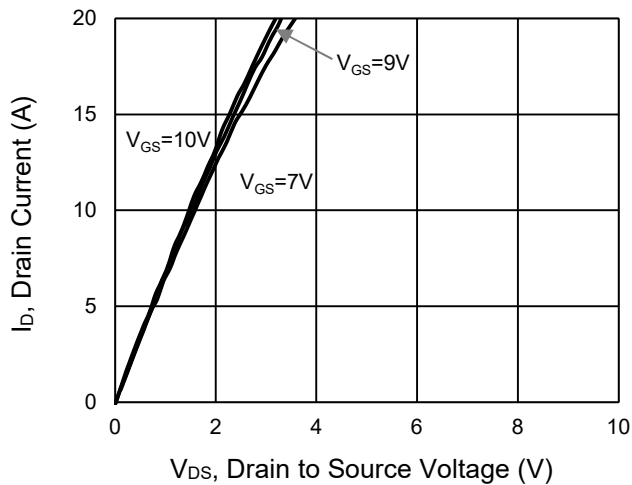
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM60NC165CI C0G	ITO-220	50pcs / Tube

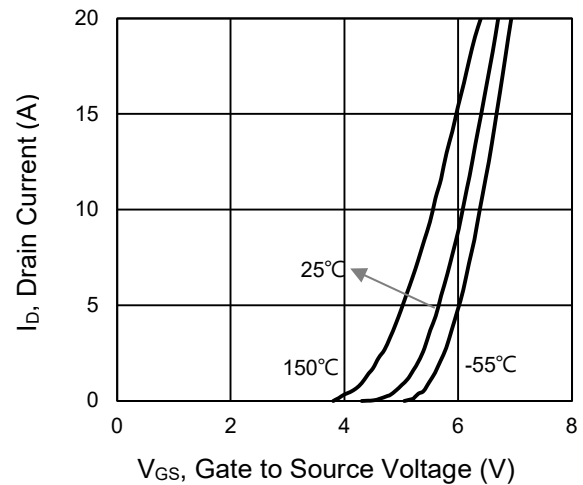
CHARACTERISTICS CURVES

($T_c = 25^\circ\text{C}$ unless otherwise noted)

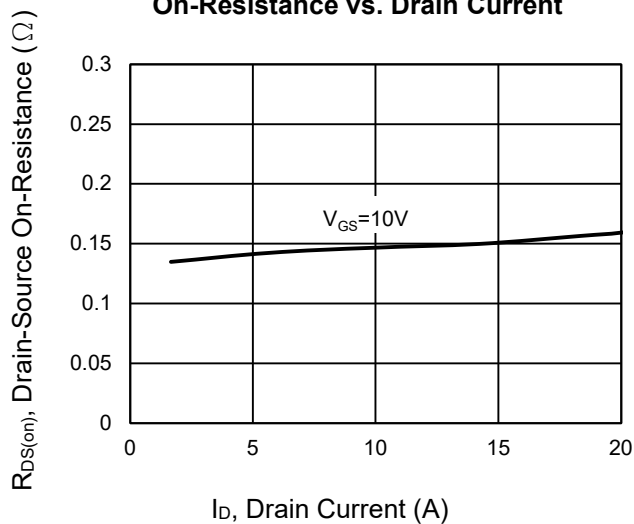
Output Characteristics



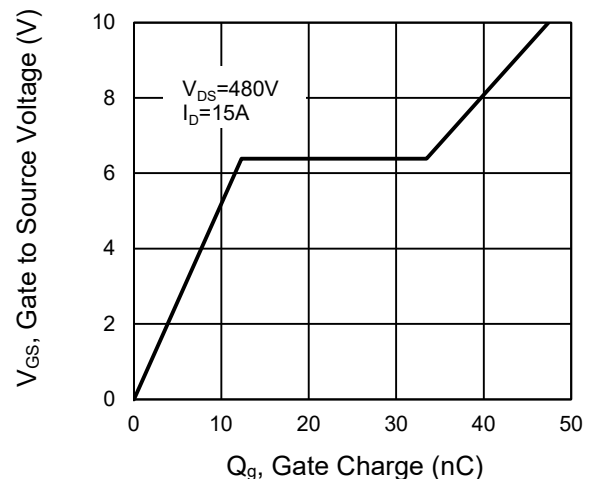
Transfer Characteristics



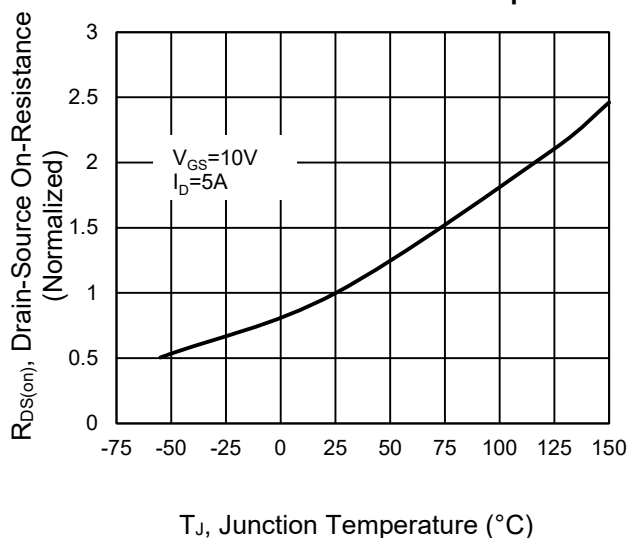
On-Resistance vs. Drain Current



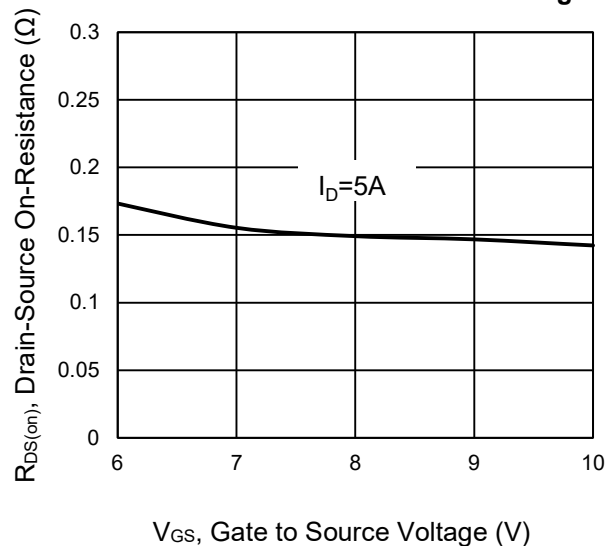
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



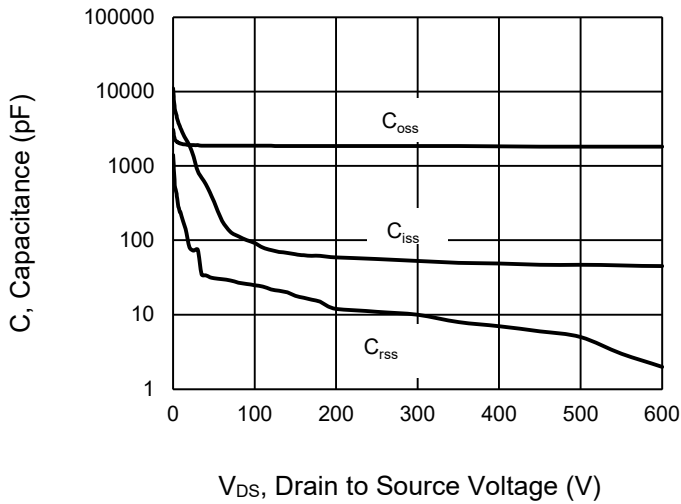
On-Resistance vs. Gate-Source Voltage



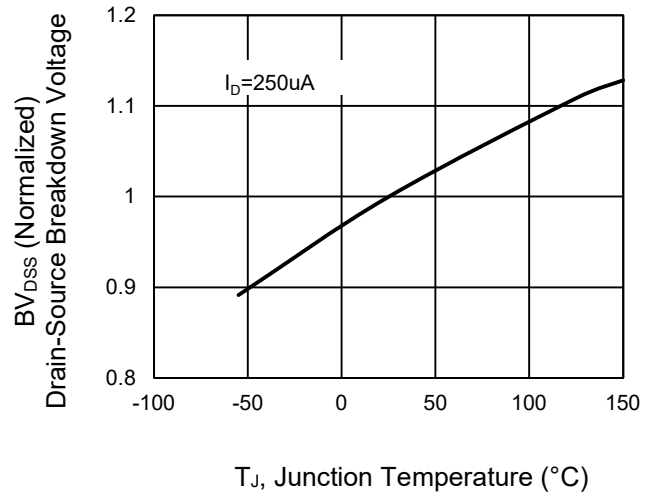
CHARACTERISTICS CURVES

($T_C = 25^\circ\text{C}$ unless otherwise noted)

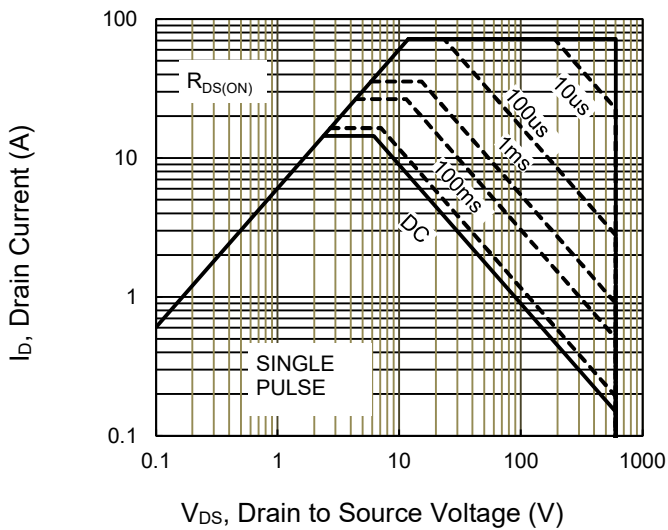
Capacitance vs. Drain-Source Voltage



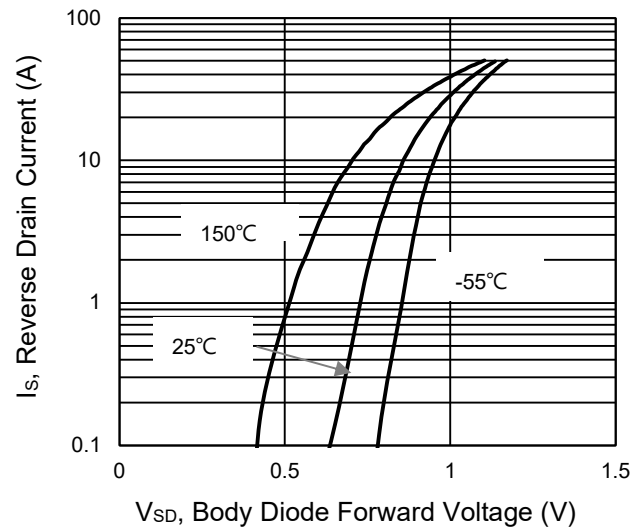
BV_{DSS} vs. Junction Temperature



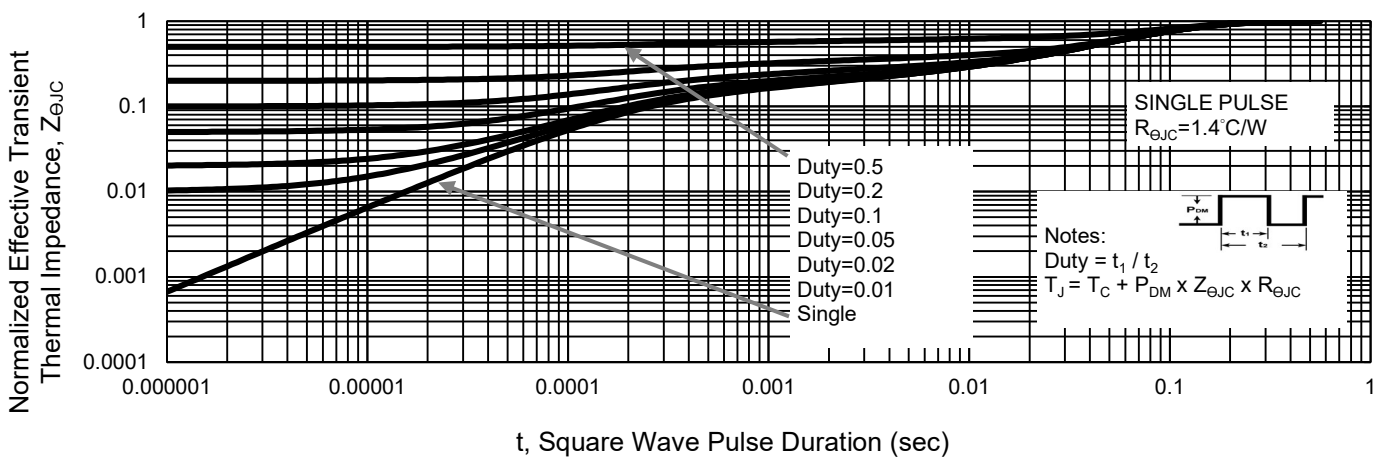
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage

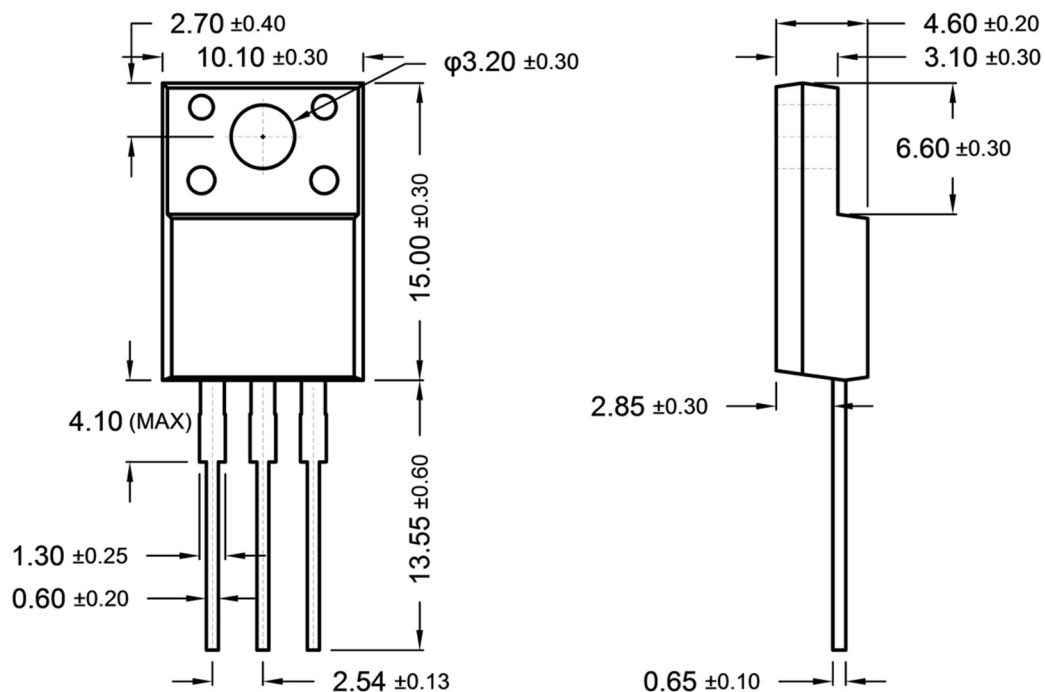


Normalized Thermal Transient Impedance, Junction-to-Case

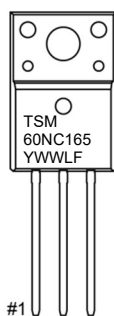


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

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MARKING DIAGRAM



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